

NTB5605P, NTB5605

MOSFET – Power, P-Channel, D²PAK

-60 V, -18.5 A

Features

- Designed for Low $R_{DS(on)}$
- Withstands High Energy in Avalanche and Commutation Modes
- AEC Q101 Qualified – NTB5605
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supplies
- PWM Motor Control
- Converters
- Power Management

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | | | Symbol | Value | Unit |
|---|------------------------|--------------------------|----------------|------------|------------------|
| Drain-to-Source Voltage | | | V_{DSS} | -60 | V |
| Gate-to-Source Voltage | | | V_{GS} | ± 20 | V |
| Continuous Drain Current (Note 1) | Steady State | $T_A = 25^\circ\text{C}$ | I_D | -18.5 | A |
| Power Dissipation (Note 1) | Steady State | $T_A = 25^\circ\text{C}$ | P_D | 88 | W |
| Pulsed Drain Current | $t_p = 10 \mu\text{s}$ | | I_{DM} | -55 | A |
| Operating Junction and Storage Temperature | | | T_J, T_{STG} | -55 to 175 | $^\circ\text{C}$ |
| Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 25 \text{ V}, V_{GS} = 5.0 \text{ V}, I_{PK} = 15 \text{ A}, L = 3.0 \text{ mH}, R_G = 25 \Omega$) | | | E_{AS} | 338 | mJ |
| Lead Temperature for Soldering Purposes (1/8 in from case for 10 s) | | | T_L | 260 | $^\circ\text{C}$ |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Max | Unit |
|---|-----------------|-----|---------------------------|
| Junction-to-Case (Drain) – Steady State | $R_{\theta JC}$ | 1.7 | $^\circ\text{C}/\text{W}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

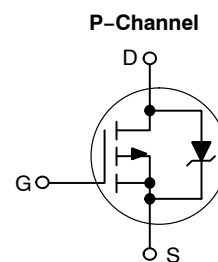
1. When surface mounted to an FR4 board using 1" pad size (Cu Area 1.127 in²).
2. When surface mounted to an FR4 board using the minimum recommended pad size (Cu Area 0.41 in²).



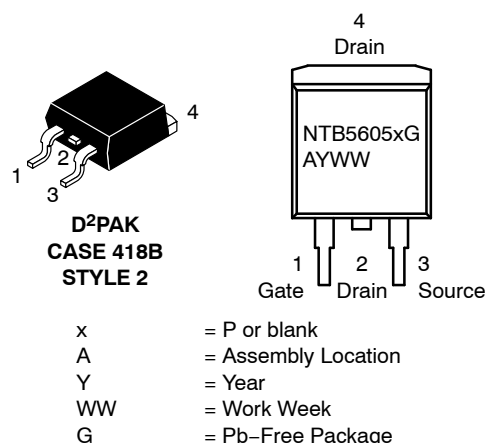
ON Semiconductor®

<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(on)}$ TYP | I_D MAX |
|---------------|-------------------------|-----------|
| -60 V | 120 m Ω @ -5.0 V | -18.5 A |



MARKING DIAGRAM & PIN ASSIGNMENT



ORDERING INFORMATION

| Device | Package | Shipping† |
|-------------|------------------------------|-------------------|
| NTB5605PT4G | D ² PAK (Pb-Free) | 800 / Tape & Reel |
| NTBV5605T4G | D ² PAK (Pb-Free) | 800 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|----------------|--------|----------------|-----|-----|-----|------|
|----------------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|---|--------------------------------------|--|------------------------|-----|------|-------|
| Drain-to-Source Breakdown Voltage | V _{(Br)DSS} | V _{GS} = 0 V, I _D = -250 μA | -60 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(Br)DSS} /T _J | | | -64 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V V _{DS} = -60 V | T _J = 25°C | | -1.0 | μA |
| | | | T _J = 125°C | | -10 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | | | ±100 | nA |

ON CHARACTERISTICS (Note 3)

| | | | | | | |
|-------------------------------|---------------------|---|------|------------|------|----|
| Gate Threshold Voltage | V _{GS(th)} | V _{GS} = V _{DS} , I _D = -250 μA | -1.0 | -1.5 | -2.0 | V |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = -5.0 V, I _D = -8.5 A V _{GS} = -5.0 V, I _D = -17 A | | 120 140 | 140 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} = -10 V, I _D = -8.5 A | | 12 | | S |
| Drain-to-Source On Voltage | V _{DS(on)} | V _{GS} = -5.0 V, I _D = -8.5 A | | | -1.3 | V |

CHARGES, CAPACITANCES AND GATE RESISTANCE

| | | | | | | |
|------------------------------|---------------------|--|--|-----|------|----|
| Input Capacitance | C _{iss} | V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = -25 V | | 730 | 1190 | pF |
| Output Capacitance | C _{oss} | | | 211 | 300 | |
| Reverse Transfer Capacitance | C _{rss} | | | 67 | 120 | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = -5.0 V, V _{DS} = -48 V, I _D = -17 A | | 13 | 22 | nC |
| Gate-to-Source Charge | Q _{GS} | | | 4.0 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 7.0 | | |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|---------------------|---------------------|--|--|------|-----|----|
| Turn-On Delay Time | t _{d(on)} | V _{GS} = -5.0 V, V _{DD} = -30 V, I _D = -17 A, R _G = 9.1 Ω | | 12.5 | 25 | ns |
| Rise Time | t _r | | | 122 | 183 | |
| Turn-Off Delay Time | t _{d(off)} | | | 29 | 58 | |
| Fall Time | t _f | | | 75 | 150 | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|-----------------|--|------------------------|------|-------|------|----|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V I _S = -17 A | T _J = 25°C | | -1.55 | -2.5 | V |
| | | | T _J = 125°C | | -1.4 | | |
| Reverse Recovery Time | t _{rr} | V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = -17 A | | 60 | | ns | |
| Charge Time | t _a | | | 39 | | | |
| Discharge Time | t _b | | | 21 | | | |
| Reverse Recovery Charge | Q _{RR} | | | 0.14 | | | nC |

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

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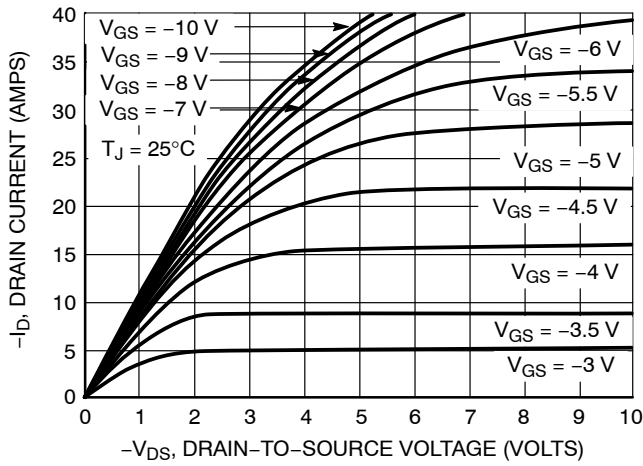


Figure 1. On-Region Characteristics

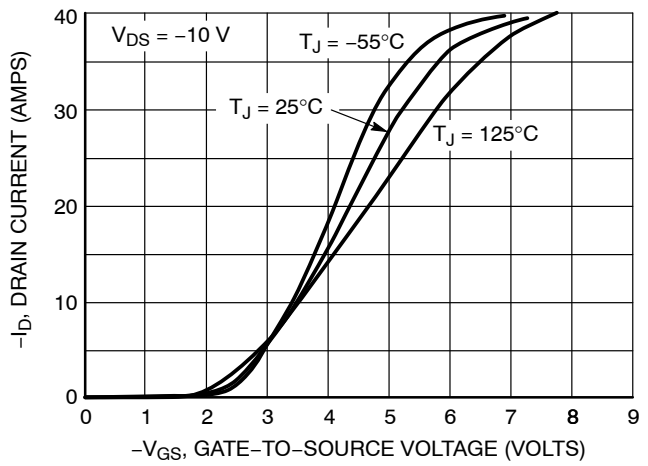


Figure 2. Transfer Characteristics

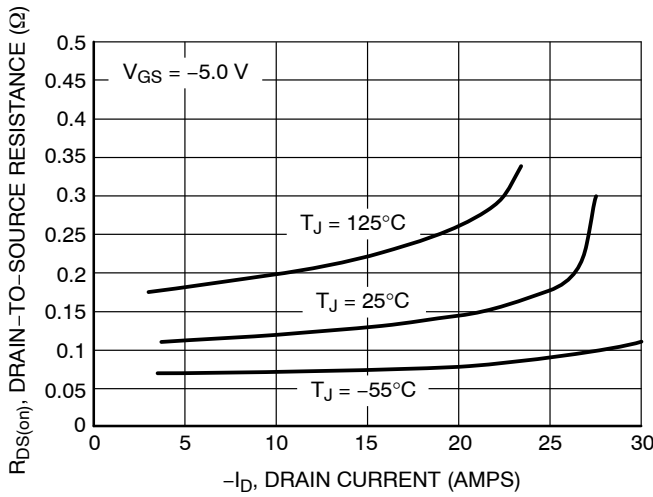


Figure 3. On-Resistance vs. Drain Current and Temperature

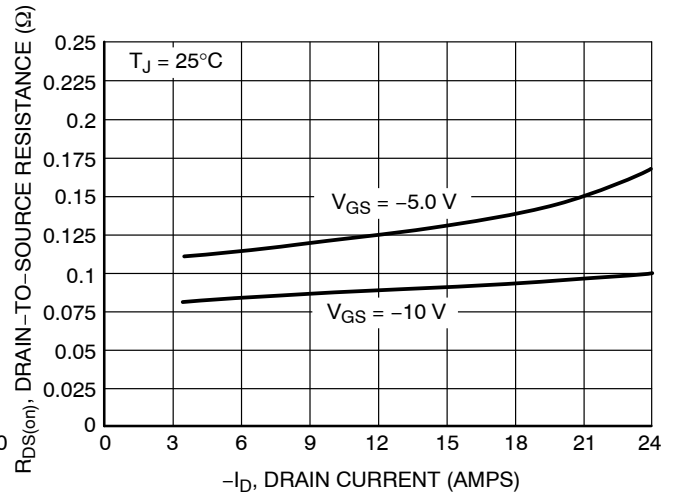


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

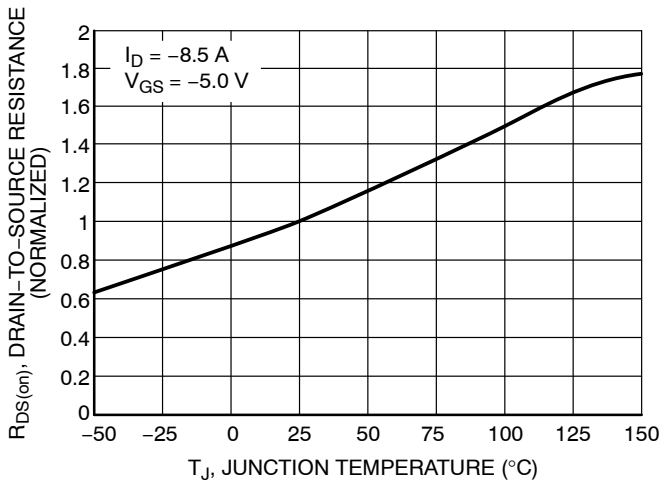


Figure 5. On-Resistance Variation with Temperature

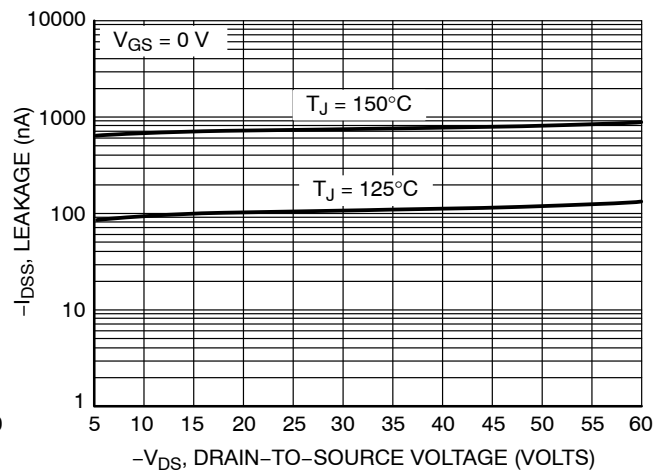


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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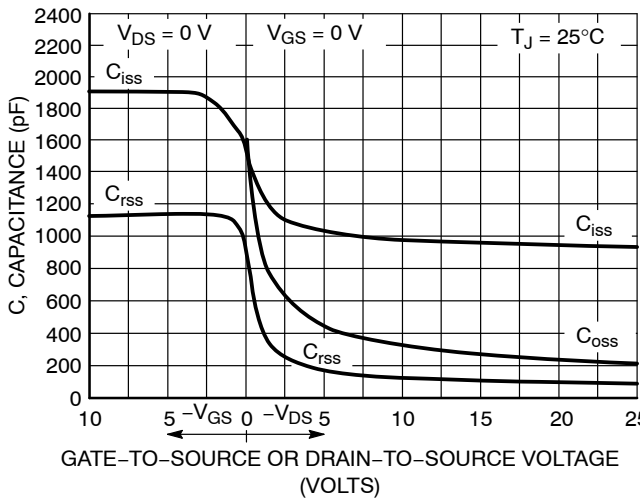


Figure 7. Capacitance Variation

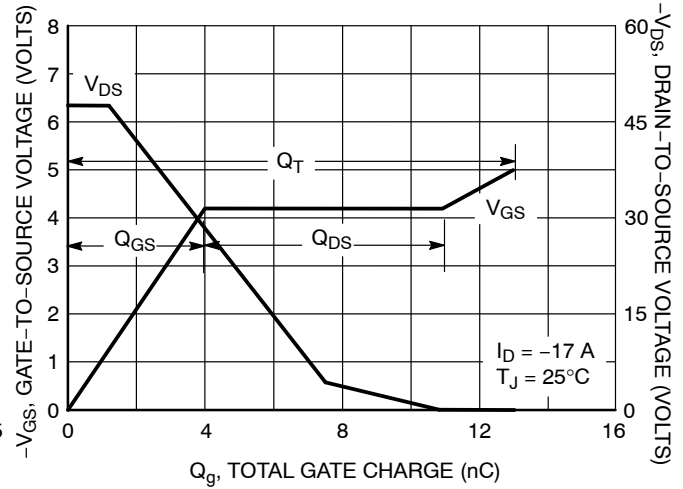


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

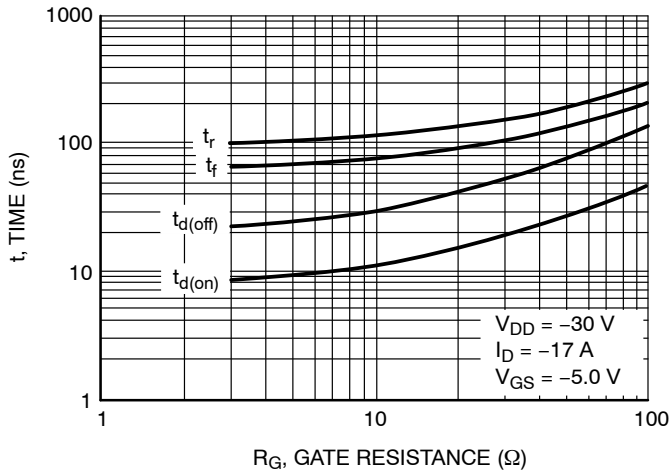


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

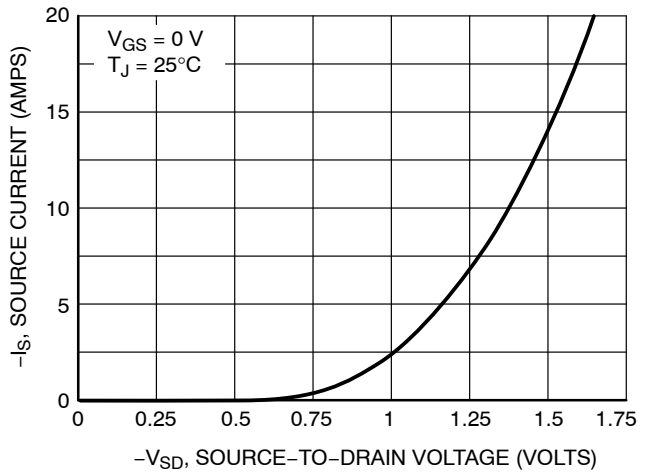


Figure 10. Diode Forward Voltage vs. Current

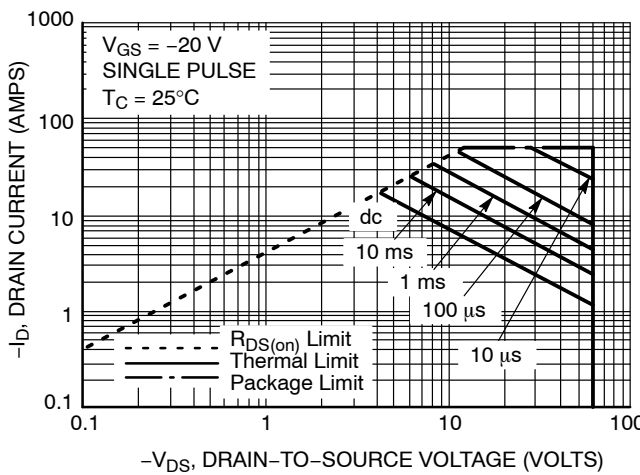


Figure 11. Maximum Rated Forward Biased Safe Operating Area

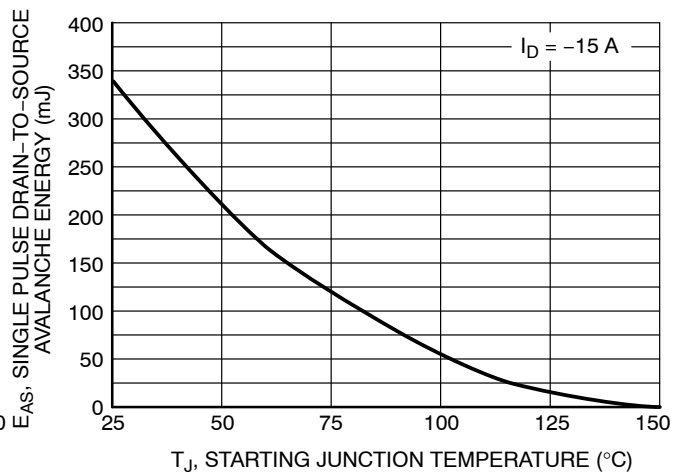


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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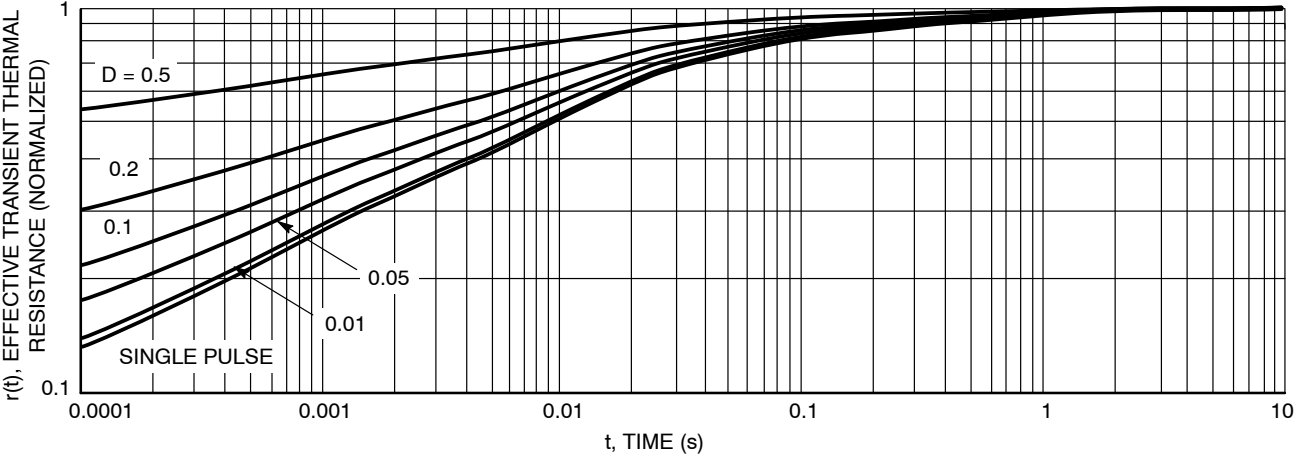


Figure 13. Thermal Response

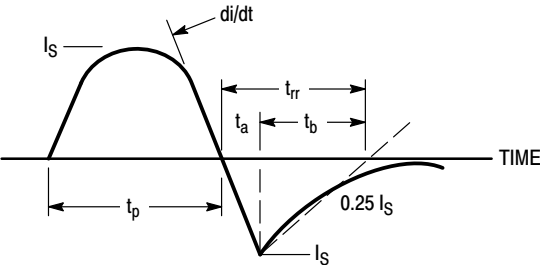


Figure 14. Diode Reverse Recovery Waveform

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

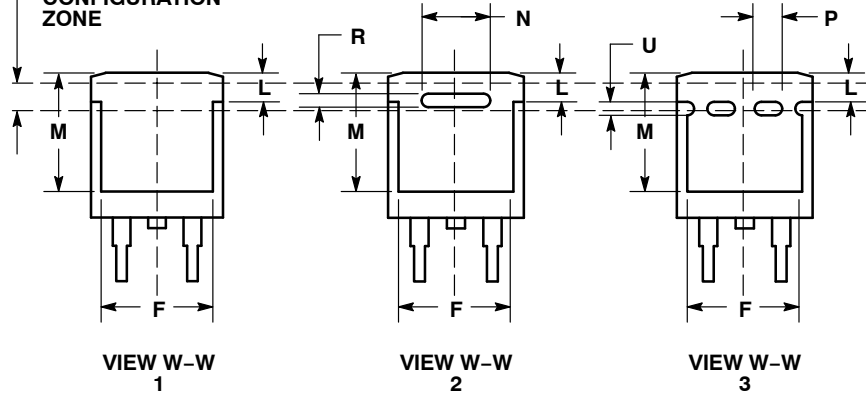


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.340 | 0.380 | 8.64 | 9.65 |
| B | 0.380 | 0.405 | 9.65 | 10.29 |
| C | 0.160 | 0.190 | 4.06 | 4.83 |
| D | 0.020 | 0.035 | 0.51 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.310 | 0.350 | 7.87 | 8.89 |
| G | 0.100 | BSC | 2.54 | BSC |
| H | 0.080 | 0.110 | 2.03 | 2.79 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.090 | 0.110 | 2.29 | 2.79 |
| L | 0.052 | 0.072 | 1.32 | 1.83 |
| M | 0.280 | 0.320 | 7.11 | 8.13 |
| N | 0.197 | REF | 5.00 | REF |
| P | 0.079 | REF | 2.00 | REF |
| R | 0.039 | REF | 0.99 | REF |
| S | 0.575 | 0.625 | 14.60 | 15.88 |
| V | 0.045 | 0.055 | 1.14 | 1.40 |

VARIABLE CONFIGURATION ZONE



- | | | | | | |
|--|---|---|--|---|--|
| STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR | STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN | STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE | STYLE 4: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR | STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE | STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE |
|--|---|---|--|---|--|

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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

**GENERIC
MARKING DIAGRAM***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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